

MICRO ELECTRONICS 2SA673

SILICON
TRANSISTOR

2SA673 is PNP silicon epitaxial transistor design for medium power amplifiers and switching applications.



ECB

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	VCBO	35V
Collector-Emitter Voltage	VCEO	35V
Emitter-Base Voltage	VEBO	4V
Collector Current	IC	500mA
Total Power Dissipation	Ptot	400mW
Operating Junction & Storage Temperature	Tj, Tstg	-55 to +150°C

ELECTRICAL CHARACTERISTICS (TA=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector Cutoff Current	ICBO		500	nA	VCB=20V IE=0
D.C. Current Gain	HFE	60	320		IC=10mA VCE=3V
Collector-Emitter Saturation Voltage	VCE(sat)		0.4	V	IC=100mA IB=10mA*
Base-Emitter Saturation Voltage	VBE(sat)		1	V	IC=100mA IB=10mA*
Collector-Base Breakdown Voltage	BVCBO	35		V	IC=100μA IE=0
Collector-Emitter Breakdown Voltage	LVCEO	35		V	IC=10mA IB=0
Emitter-Base Breakdown Voltage	BVEBO	4		V	IE=100μA IC=0
Current Gain-Bandwidth Product	fT	120 TYP.		MHz	IC=10mA VCE=10V
Output Capacitance	Cob		7TYP.	pF	VCB=10V f=1MHz



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* Pulse test.

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1-1-BmP

This datasheet has been download from:

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Datasheets for electronics components.